L Number	Hits	Search Text	DB	Time stamp
3	1480	(257/316).ccls. and @ad<=20010323	USPAT;	2004/03/18
			US-PGPUB;	16:52
			EPO; JPO;	
			DERWENT;	
6	474	(257/303).ccls. and @ad<=20010323	USPAT;	2004/03/18
*		(2017,000,100251 and gam 1 20020020	US-PGPUB;	16:52
			EPO; JPO;	
			DERWENT;	
7	155	(257/929).ccls. and @ad<=20010323	IBM_TDB USPAT;	2004/03/18
′	133	(2577929).ccis. and ead(-20010323	US-PGPUB;	16:53
			EPO; JPO;	
			DERWENT;	
		/420/000\	IBM_TDB	2004/03/10
8	51	(438/222).ccls. and @ad<=20010323	USPĀT; US-PGPUB;	2004/03/18
			EPO; JPO;	10.37
			DERWENT;	,
			IBM_TDB	
9	876	(257/368).ccls. and @ad<=20010323	USPAT;	2004/03/18
			US-PGPUB; EPO; JPO;	16:54
			DERWENT;	
			IBM_TDB	
10	42	(257/41).ccls. and @ad<=20010323	USPĀT;	2004/03/18
			US-PGPUB;	16:54
			EPO; JPO; DERWENT;	
			IBM TDB	
11	34	(257/44).ccls. and @ad<=20010323	USPĀT;	2004/03/18
			US-PGPUB;	16:56
			EPO; JPO; DERWENT;	
			IBM TDB	,
12	751	(257/288).ccls. and @ad<=20010323	USPAT;	2004/03/18
			US-PGPUB;	16:57
			EPO; JPO;	
			DERWENT; IBM TDB	
13	732	(257/592).ccls. and @ad<=20010323	USPAT;	2004/03/18
			US-PGPUB;	16:57
			EPO; JPO;	
			DERWENT; IBM TDB	
14	242	(438/350).ccls. and @ad<=20010323	USPAT;	2004/03/18
			US-PGPUB;	16:57
			EPO; JPO;	
			DERWENT;	
_	10	(("5393681") or ("6391692") or	IBM_TDB USPAT;	2003/06/25
		("5308782") or ("5998248") or	US-PGPUB;	06:43
		("6319782")).PN.	EPO; JPO;	
			DERWENT;	
l _	162	 257/929 and @ad<=20010323	IBM_TDB USPAT;	2003/06/24
1	102	201, 525 and caux-20010323	US-PGPUB;	14:45
1			EPO; JPO;	,
			DERWENT;	
	542	438/300 and @ad<=20010323	IBM_TDB USPAT;	2003/06/24
-	342	430/300 and wad\-20010323	US-PGPUB;	14:44
1	1		EPO; JPO;	
			DERWENT;	
		0.14.00010000	IBM_TDB	2002/00/04
-	4	@ad<=20010323 and 'raised vertical lateral transistor'	USPAT; US-PGPUB;	2002/09/04 16:02
		Taccial Classistot	EPO; JPO;	10.02
1	1		DERWENT;	
			IBM_TDB	

			. %.=	
-	1	@ad<=20010323 and 'raised source and drain'	USPAT; US-PGPUB;	2002/09/04 15:26
			EPO; JPO; DERWENT;	ė
_	1	 @ad<=20010323 and 'epitaxial' and 'source	IBM_TDB USPAT;	2002/09/04
		or drain'	US-PGPUB; EPO; JPO;	15:30
			DERWENT;	
_	8	• · · · · · · · · · · · · · · · · · ·	IBM_TDB USPAT;	2002/09/04
:		and drain'	US-PGPUB; EPO; JPO;	15:30
			DERWENT; IBM TDB	
_	3470	gardner.inv.	USPAT;	2002/09/04 15:45
			US-PGPUB; EPO; JPO;	15:45
			DERWENT; IBM TDB	
-	6	gardner.inv. and 'vertical transistor'	USPAT; US-PGPUB;	2002/09/04 15:48
		and Gad (=20010323	EPO; JPO;	13.10
			DERWENT; IBM_TDB	
-	4	@ad<=20010323 and 'elevated source and drain'	USPAT; US-PGPUB;	2003/03/25 14:24
			EPO; JPO; DERWENT;	·
	257		IBM_TDB USPAT;	2002/09/04
-	257	Gad<=20010323 and elevated source	US-PGPUB;	16:06
			EPO; JPO; DERWENT;	
_	37	@ad<=20010323 and 'epitaxial' with	IBM_TDB USPAT;	2003/06/24
		'elevated source'	US-PGPUB; EPO; JPO;	14:23
			DERWENT;	
_	1	"4728623".PN.	IBM_TDB USPAT	2002/09/04
_	1	"4738937".PN.	USPAT	16:31 2002/09/04
_	1	"4918029".PN.	USPAT	16:31 2002/09/04
_	1	"5004702".PN.	USPAT	16:31 2002/09/04
_	1	"5030583".PN.	USPAT	16:31 2002/09/04
	1	"5032538".PN.	USPAT	16:31
	_			16:31
-	1	"5045494".PN.	USPAT	2002/09/04
-	1	"5272109".PN.	USPAT	2002/09/04 16:32
-	1	"5496750".PN.	USPAT	2002/09/04 16:38
	1	"5378651".PN.	USPAT	2002/09/04 16:38
-	1	"5321306".PN.	USPAT	2002/09/04
-	1	"5296388".PN.	USPAT	2002/09/04
_	1	"5250454".PN.	USPAT	16:38
_	1	"5213991".PN.	USPAT	16:39 2002/09/04
_	1	"5079180".PN.	USPAT	16:39 2002/09/04
-	1	"5057899".PN.	USPAT	16:39 2002/09/04
				16:39

	-	HADCCOC1 H DV	110000	1 2000 /60 /01
_	1	"4966861".PN.	USPAT	2002/09/04 16:41
-	1	"4814841".PN.	USPAT	2002/09/04
-	1	"5057893".РМ.	USPAT	2002/09/04
-	18	(("6096596") or ("6090691") or ("5998844")	USPAT; US-PGPUB;	2002/09/05
		or ("5963822") or ("5945698") or ("5933738") or ("5863826")).PN.	EPO; JPO; DERWENT;	
			IBM_TDB	
-	18	(("5831334") or ("5677573") or ("5641694") or ("5600161") or ("5497017")	USPAT; US-PGPUB;	2002/09/05
		or ("5312768") or ("5156987") or ("5122476") or ("5087586")).PN.	EPO; JPO; DERWENT;	
	_	("5308782").PN.	IBM_TDB USPAT;	2002/09/05
_	2	("5308/82").PN.	US-PGPUB;	10:19
			EPO; JPO; DERWENT;	
_	2	("6319782").PN.	IBM_TDB USPAT;	2002/09/05
	_	,	US-PGPUB; EPO; JPO;	10:19
			DERWENT;	
_	1731	((438/300) or (257/302) or (257/929) or	IBM_TDB USPAT;	2002/11/20
		(257/592)).CCLS.	US-PGPUB; EPO; JPO;	08:44
			DERWENT; IBM TDB	
_	12	ri-seiko.in.	USPĀT;	2002/11/20
			US-PGPUB; EPO; JPO;	08:44
			DERWENT; IBM_TDB	
-	38	<pre>@ad<=20010323 and 'epitaxial' with 'elevated source'</pre>	USPĀT; US-PGPUB;	2002/11/20 09:33
			EPO; JPO; DERWENT;	
	0.60	A-4-20010222 and 1-1-2	IBM_TDB	2002/11/20
_	263	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB;	2002/11/20 09:33
			EPO; JPO; DERWENT;	
_	263	 @ad<=20010323 and elevated adj1 source	IBM_TDB USPAT;	2002/11/20
			US-PGPUB; EPO; JPO;	09:02
			DERWENT; IBM TDB	
_	95	@ad<=20010323 and elevated adj1 drain	USPAT;	2002/11/20
			US-PGPUB; EPO; JPO;	09:02
			DERWENT; IBM_TDB	
-	112	@ad<=20010323 and raised adj1 drain	USPAT; US-PGPUB;	2002/11/20
			EPO; JPO; DERWENT;	
			IBM_TDB	2002/11/22
-	229	@ad<=20010323 and raised adj1 source	USPAT; US-PGPUB;	2002/11/20 09:03
			EPO; JPO; DERWENT;	
_	0	@ad<=20010323 and 'epitaxial silicon	IBM_TDB USPAT;	2002/11/20
		gate' with 'elevated source'	US-PGPUB;	09:38
			EPO; JPO; DERWENT;	
			IBM TDB	

-	20		USPAT;	2002/11/20
		'elevated source'	US-PGPUB;	09:38
			EPO; JPO;	
	1		DERWENT;	
	1	<u> </u>	IBM_TDB	
-	47	@ad<=20010323 and 'polysilicon gate' and	USPAT;	2003/03/25
İ		'elevated source'	US-PGPUB;	14:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	•	USPAT;	2003/03/25
		gate' and 'elevated source'	US-PGPUB;	14:25
			EPO; JPO;	_
			DERWENT;]
	1	0-4-20010222	IBM_TDB	2002/11/20:
-	1	<pre>@ad<=20010323 and 'epitaxial polysilicon' and 'elevated source'</pre>	USPAT;	2002/11/20
		and relevated source.	US-PGPUB;	10:08
			EPO; JPO;	
			DERWENT;	
l _	56	@ad<=20010323 and 'epitaxial polysilicon'	IBM_TDB USPAT;	2002/11/21
1	30	eau\-20010323 and epitaxial polysilicon	US-PGPUB;	08:20
	1		EPO; JPO;	00.20
			DERWENT;	·
			IBM TDB	
l _	0	@ad<=20010323 and 'epitaxial polysilicon	USPAT;	2002/11/20
	1	gate'	US-PGPUB;	14:05
1		gace	EPO; JPO;	11.00
			DERWENT;	
			IBM TDB	
_	24	@ad<=20010323 and 'epitaxial gate'	USPAT;	2002/11/20
			US-PGPUB;	14:05
			EPO; JPO;	
			DERWENT;	
	<u> </u>		IBM TDB	
_	24	@ad<=20010323 and 'epitaxial gate'	USPAT;	2002/11/21
			US-PGPUB;	08:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	560		USPAT;	2002/11/20
		epitaxial with gate	US-PGPUB;	16:16
			EPO; JPO;	
	}		DERWENT;]
			IBM_TDB	2002/11/21
-	2348	@ad<=20010323 and 'multilayer' same	USPAT;	2002/11/21
	1	'gate'	US-PGPUB;	08:55
	1		EPO; JPO;	
	1		DERWENT;	
I _	260	[[[]]] [] [] [] [] [] [] []	IBM_TDB USPAT;	2002/11/20
1 -	200	(@ad<=20010323 and 'multilayer' same 'gate') and 'epitaxial'	US-PGPUB;	16:18
1	[gate / and epitaniai	EPO; JPO;	10.10
1	1		DERWENT;	1
			IBM TDB	
l _	0	@ad<=20010323 and 'multilayer gate' with	USPAT;	2003/06/25
	1	'epitaxial'	US-PGPUB;	08:33
		•	EPO; JPO;	
1	1		DERWENT;	
	1		IBM TDB	
-	1		USPAT;	2002/11/21
[near polysilicon	US-PGPUB;	08:20
1	1		EPO; JPO;	
1	İ		DERWENT;	
	1		IBM_TDB	
-	693	l [*]	USPAT;	2002/11/21
		same 'gate'	US-PGPUB;	08:32
	1		EPO; JPO;	
	1		DERWENT;	
L	<u> </u>	<u> </u>	IBM TDB	<u> </u>

-	367	@ad<=20010323 and 'epitaxial silicon' with 'gate'	USPAT; US-PGPUB;	2002/11/21 08:41
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB;	2003/03/26
		gate	EPO; JPO;	10.14
			DERWENT; IBM TDB	
_	1	@ad<=20010323 and 'multilayer silicon	USPAT;	2002/11/21
1		gate'	US-PGPUB;	08:56
			EPO; JPO; DERWENT;	
	_		IBM_TDB	
_	1	("6534809").PN.	USPAT; US-PGPUB;	2003/03/25 13:55
			EPO; JPO;	13.33
			DERWENT;	
_	564	 @ad<=20010323 and 'polysilicon gate' same	IBM_TDB USPAT;	2003/03/25
		'epitaxial'	US-PGPUB;	14:18
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	390	(257/756).ccls and @ad<=20010323	USPĀT;	2003/06/24
			US-PGPUB; EPO; JPO;	14:43
			DERWENT;	
_	214	 @ad<=20010323 and 'floating gate' same	IBM_TDB USPAT;	2003/03/25
		'epitaxial'	US-PGPUB;	14:18
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2141	@ad<=20010323 and 'elevated' same	USPAT;	2003/03/25
		'source' and 'drain'	US-PGPUB; EPO; JPO;	14:28
			DERWENT;	
_	413	 @ad<=20010323 and 'elevated' with	IBM_TDB USPAT;	2003/03/25
	113	'source' with 'drain'	US-PGPUB;	14:28
			EPO; JPO;	
			DERWENT; IBM TDB	
-	6	@ad<=20010323 and 'epi silicon' and	USPĀT;	2003/06/25
		'elevated' same 'source'	US-PGPUB; EPO; JPO;	06:45
			DERWENT;	
_	1	"4074300".PN.	IBM_TDB USPAT	2003/03/25
				14:37
_	32	<pre>@ad<=20010323 and 'gate stack' and 'elevated' same 'source'</pre>	USPAT; US-PGPUB;	2003/03/25 15:13
			EPO; JPO;	
			DERWENT; IBM TDB	
_	8	(("4583105") or ("6083815") or	USPAT;	2003/03/25
		("5885877") or ("5986328")).PN.	US-PGPUB;	15:39
			EPO; JPO; DERWENT;	
	_	(#E100370#), DV	IBM_TDB	2002/02/25
-	2	("5198378").PN.	USPAT; US-PGPUB;	2003/03/25 15:39
			EPO; JPO;	
			DERWENT; IBM TDB	
_	92	@ad<=20010323 and 'epi' and 'silicon	USPĀT;	2003/03/26
		gate'	US-PGPUB;	11:54
			EPO; JPO; DERWENT;	
			IBM TDB	

-	9	@ad<=20010323 and 'epitaxial silicon	USPAT;	2003/03/26
		gate'	US-PGPUB;	11:10
			EPO; JPO;	
	:		DERWENT;	-
_	1	("6528363").PN.	IBM_TDB USPAT;	2003/03/26
	1	(0320303).PN.	US-PGPUB;	11:10
			EPO; JPO;	11110
			DERWENT;	
			IBM TDB	
_	7	@ad<=20010323 and 'conductor' same 'epi'	USPAT;	2003/03/26
		same 'polysilicon' same 'amorphous'	US-PGPUB;	14:31
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	@ad<=20010323 and 'conductive' same 'epi'	USPAT;	2003/03/26
		same 'polysilicon' same 'amorphous'	US-PGPUB;	12:04
			EPO; JPO;	
			DERWENT;	·
			IBM_TDB	
-	3	("6335251").PN.	USPAT;	2003/03/26
			US-PGPUB;	14:34
			EPO; JPO;	
			DERWENT;	
	_	(#6222641#\ pw	IBM_TDB USPAT;	2003/03/26
-	2	("6232641").PN.		
			US-PGPUB; EPO; JPO;	15:01
			DERWENT;	
			IBM TDB	
_	2	("6171910").PN.	USPAT;	2003/03/26
_		(01/1910 /.EN.	US-PGPUB;	15:20
			EPO; JPO;	10.20
<u> </u>			DERWENT;	
			IBM TDB	
-	1 2	("6051473").PN.	USPAT;	2003/03/26
1	_	,	US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8	@ad<=20010323 and 'epi silicon' and	USPAT;	2003/06/24
		'raised' same 'source'	US-PGPUB;	14:42
i			EPO; JPO;	
			DERWENT;	
		<u> </u>	IBM_TDB	
-	9	@ad<=20010323 and 'epitaxial' adj1	USPAT;	2003/06/24
		'silicon' adj1 'gate'	US-PGPUB;	14:36
			EPO; JPO;	
	1		DERWENT;	
	24	 @ad<=20010323 and 'epitaxial' adj1 'gate'	IBM_TDB USPAT;	2003/06/24
-	24	eau\-20010323 and epicaxial adji gate	US-PGPUB;	14:36
			EPO; JPO;	17.50
			DERWENT;	
			IBM TDB	
_	11	@ad<=20010323 and 'epi silicon' and	USPAT;	2003/06/24
		'raised' same 'source'	US-PGPUB;	14:42
			EPO; JPO;	
1			DERWENT;	
]		IBM TDB	
-	394	(257/756).ccls and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	600	438/300 and @ad<=20010323	USPAT;	2003/06/25
	1		US-PGPUB;	08:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	2	("6534809").PN.	USPAT;	2003/06/25
			US-PGPUB;	06:43
1			EPO; JPO;	
			DERWENT;	
		0 1. 00010000	IBM_TDB	
_	173	@ad<=20010323 and 'epitaxial' adj1	USPAT;	2004/03/18
		'silicon' and 'elevated' same 'source'	US-PGPUB;	13:32
	1		EPO; JPO;	
			DERWENT;	
		0-14 20010202 3 1 4 31 4-1	IBM_TDB	2003/06/25
-	2	<pre>@ad<=20010323 and 'epitaxial' adj1 'silicon gate' and 'elevated' same</pre>	USPAT;	2003/06/25
		'source'	US-PGPUB; EPO; JPO;	06:46
		Source	DERWENT;	.
			IBM TDB	
1_	43	<pre>@ad<=20010323 and 'gate' with 'epitaxial'</pre>	USPAT;	2003/06/25
	15	adj1 'silicon' and 'elevated' same	US-PGPUB;	07:35
		'source'	EPO; JPO;	"
			DERWENT;	
			IBM_TDB	
_	17	@ad<=20010323 and 'transistor gate' with	USPAT;	2003/06/25
]	'epitaxial' adj1 'silicon'	US-PGPUB;	07:45
		•	EPO; JPO;	
]		DERWENT;	
			IBM TDB	
_	143	@ad<=20010323 and 'transistor gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB;	09:33
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	238	@ad<=20010323 and 'epitaxial' adj2 'gate'	USPAT;	2003/06/25
	•		US-PGPUB;	08:08
1			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000 (05 (05
-	2	@ad<=20010323 and 'stacked gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB;	08:33
		_	EPO; JPO; DERWENT;	
		·	IBM TDB	
1_	243	(438/657).ccls. and @ad<=20010323	USPAT;	2004/03/18
	243	(450/05//.ccis. and ead(-20010325	US-PGPUB;	16:48
			EPO; JPO;	10110
	[DERWENT;	
]		IBM TDB	.
_	225	(438/647).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:56
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	118	(257/385).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:56
]		EPO; JPO;	
			DERWENT;	
	l <u>.</u>	(057/000)	IBM_TDB	2002/06/25
-	534	(257/382).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:59
]		EPO; JPO; DERWENT;	
			IBM TDB	
1_	225	(438/647).ccls. and @ad<=20010323	USPAT;	2003/06/25
	223	\150/041/.0015. and Gad\-20010323	US-PGPUB;	08:57
]		EPO; JPO;	
	[DERWENT;	
	1		IBM TDB	
-	313	(438/300).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:58
			EPO; JPO;	
]		DERWENT;	
I	1		IBM TDB	

-	69	(257/381).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:59
			EPO; JPO;	
			DERWENT; IBM TDB	
l _	244	(257/756).ccls. and @ad<=20010323	USPAT;	2003/06/25
	233	(2577750):ee15: and ead(-20010525	US-PGPUB;	08:59
			EPO; JPO;	
			DERWENT;	
			IBM TDB	i
-	197	@ad<=20010323 and 'polysilicon gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB;	09:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	/
-	0		USPAT;	2003/11/12
	1	with 'selected silicon'	US-PGPUB;	11:35
			EPO; JPO; DERWENT;	
			IBM TDB	
l _	238	@ad<=20010323 and 'single' with 'poly'	USPAT;	2003/11/12
		with 'amorphous'	US-PGPUB;	14:09
1			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	·
-	386		USPAT;	2003/11/12
		with 'gate'	US-PGPUB;	11:42
			EPO; JPO;	1
			DERWENT;	1
			IBM_TDB	2002/11/12
-	88	@ad<=20010323 and 'gate electrode' with	USPAT;	2003/11/12
		'epitaxial silicon'	US-PGPUB; EPO; JPO;	13:07
			DERWENT;	[
			IBM TDB	
1_	5	@ad<=20010323 and 'epitaxial' near 'gate'	USPAT;	2003/11/12
		near 'silicon'	US-PGPUB;	13:11
			EPO; JPO;	·
			DERWENT;	
			IBM_TDB	
-	68	@ad<=20010323 and 'epitaxial' near 'gate'	USPAT;	2003/11/12
•			US-PGPUB;	13:19
			EPO; JPO;	
			DERWENT;	
1	1.4	 @ad<=20010323 and 'epitaxial silicon'	IBM_TDB USPAT;	2003/11/12
-	14	dad<=20010323 and repitaxial sillcon near 'gate'	US-PGPUB;	13:19
1		near yave	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	187	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		near4 'gate'	US-PGPUB;	13:47
			EPO; JPO;	.
			DERWENT;	
			IBM_TDB	2002/11/10
-	138		USPAT;	2003/11/12
		near3 'gate'	US-PGPUB; EPO; JPO;	13:20
ļ			DERWENT;	
			IBM TDB	
_	2	("6534809").PN.	USPAT;	2003/11/12
		,	US-PGPUB;	13:47
	1		EPO; JPO;	
]	1		DERWENT;	
	ļ		IBM_TDB	
-	428	@ad<=20010323 and 'schottky gate' and	USPAT;	2003/11/12
		'epitaxial'	US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
L	l		IBM TDB	

			_	*
_	8	@ad<=20010323 and 'schottky gate' and 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO;	2003/11/12
	•		DERWENT;	
_	1971	@ad<=20010323 and 'epitaxial silicon'	IBM_TDB USPAT;	2003/11/12
	1371	nearl 'layers'	US-PGPUB; EPO; JPO;	14:34
			DERWENT; IBM TDB	
_	13	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		nearl 'layers' nearl 'gate'	US-PGPUB;	14:34
Ì			EPO; JPO;	
			DERWENT; IBM TDB	
_	65	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		near1 'layers' near2 'gate'	US-PGPUB;	15:11
			EPO; JPO;	
			DERWENT; IBM TDB	
l _	2	("5110748").PN.	USPAT;	2003/11/12
			US-PGPUB;	15:37
			EPO; JPO; DERWENT;	
			IBM TDB	
-	1	"3959045".PN.	USPĀT	2003/11/12
		#2007201# PV	TICDAM.	15:12 2003/11/12
-	1	"3997381".PN.	USPAT	15:12
_	1	"4292730".PN.	USPAT	2003/11/12
	_			15:13
-	1	"4888304".PN.	USPAT	2003/11/12 15:13
_	1	"4891329".PN.	USPAT	2003/11/12
			110030	15:14
_	1	"4983251".PN.	USPAT	2003/11/12 15:14
_	1	"5006487".PN.	USPAT	2003/11/12
		W5 00 C40 7 W DV	USPAT	15:15 2003/11/12
-	1	"5006487".PN.	USPAI	15:16
_	1	"5013681".PN.	USPAT	2003/11/12
		(Harrist de Landa de H.) DAY	USPAT;	15:17 2003/11/12
_	0	("candelaria.in.").PN.	US-PGPUB;	15:38
			EPO; JPO;	
			DERWENT;	
_	0	("candelaria-jon.in.").PN.	IBM_TDB USPAT;	2003/11/12
	Ĭ	Canadialia jonilia / ini	US-PGPUB;	15:37
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	("candelaria-jon-j.in.").PN.	USPAT;	2003/11/12
	}		US-PGPUB;	15:38
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	0	("Candelaria-jon-j.in.").PN.	USPAT;	2003/11/12
			US-PGPUB; EPO; JPO;	15:39
			DERWENT;	
			IBM_TDB	2002/11/12
-	65	candelaria.in.	USPAT; US-PGPUB;	2003/11/12 15:38
			EPO; JPO;	
			DERWENT;	
		_	IBM TDB	

- 6 Candelaria-jon-j.in. USPAT; 2003/1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2004/0 US-PGPUB; 09:22 EPO; JPO;	
EPO; JPO; DERWENT; IBM_TDB USPAT; 2004/0 US-PGPUB; 09:22	03/18
DERWENT; IBM_TDB USPAT; US-PGPUB; 09:22)3/18
IBM_TDB USPAT; 2004/0 USPAT; US-PGPUB; 09:22)3/18
- 2 "20020137269" USPĀT; 2004/0 US-PGPUB; 09:22	03/18
US-PGPUB; 09:22	73/18
	÷
EPO; UPO;	+
DEDURAM.	
DERWENT; IBM TDB	
- 2 "20020093054" USPAT; 2004/0	13/18
US-PGPUB; 10:09	/3/10
EPO; JPO;	
DERWENT;	
IBM TDB	
- 2 "20010019137" USPAT; 2004/0	3/18
US-PGPUB; 10:11	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 2 ("6630721").PN. USPAT; 2004/0)3/18
US-PGPUB; 10:13	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 2 ("6433382").PN. USPAT; 2004/0)3/18
US-PGPUB; 10:26	
EPO; JPO;	
DERWENT;	
	12/19
- 1 "5739567".PN. USPAT 2004/0	/3/10
_ 1 "5627395".PN. USPAT 2004/0	13/18
1 3627393 :FN: 10:34	.
_ 2 ("6150688").PN. USPAT; 2004/0)3/18
US-PGPUB; 10:33	
EPO; JPO;	•
DERWENT,	
IBM_TDB	
- 2 ("6037202").PN. USPĀT; 2004/0)3/18
US-PGPUB; 10:34	
EPO; JPO;	
DERWENT;	
IBM_TDB	22/10
- 22 (("5994735") or ("5886382") or USPAT; 2004/0	12/18 .
("5780327") or ("5612563") or ("5612230") US-PGPUB; 10:49	
or ("5595920") or ("5578850") or EPO; JPO;	
("5574299") or ("4447889") or ("5483094") DERWENT; or ("5460994")).PN.	.
or ("5460994")).PN. 108 @ad<=20010323 and 'vertical' with USPAT; 2004/0	13/18
'transistor' same 'epitaxial silicon' US-PGPUB; 13:34	, , , , ,
EPO; JPO;	ļ
DERWENT;	
IBM TDB	
- 47 @ad<=20010323 and 'vertical' with USPAT; 2004/6	03/18
'transistor' with 'epitaxial silicon' US-PGPUB; 13:34	
EPO; JPO;	.
DERWENT;	
IBM TDB	